

Session Program

16-18 Nov 2009

15th RD50 Workshop

***Pad Detector Characterization & Studies on
Charge Multiplication***

CERN, TE Auditorium

Tuesday 17 November

09:15

Pad Detector Characterization & Studies on Charge Multiplication

Session | Location: CERN, TE Auditorium

09:15-09:35

Mixed irradiation studies with magnetic czochralski diodes

Speaker

Robert Eber

09:35-09:55

Results on diodes

Speaker

Katharina Kaska

09:55-10:15

Charge Collection and Trapping in Epitaxial Silicon Detectors after Neutron Irradiation

Speaker

Mr Thomas Pohlson

10:15-10:35

CCE in irradiated silicon detectors with a consideration of avalanche effect

Speaker

Dr Vladimir Eremin

10:35-11:05

Coffee break

11:05-11:25

Detailed investigation of charge multiplication properties in highly irradiated thin epitaxial silicon diodes

Speaker

Jörn Lange

11:25-11:45

Investigation of electric field and charge multiplication in irradiated silicon detectors by Edge-TCT

Speaker

Gregor Kramberger

11:45-12:00

Effects of annealing on charge collection in heavily irradiated silicon micro-strip detectors

Speaker

Marko MILOVANOVIĆ

12:00-12:15

Recent results of annealing measurements in p-type microstrip detector with SCT128 chip (Late submission)

Speaker

Igor Mandic

12:30

12:15-12:30

Discussion: Pad Detectors and Charge Multiplication